Observation of three-dim ensional bulk Ferm i surfaces for a strongly correlated m aterial by soft x-ray h -dependent (700-860 eV) ARPES

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Three-dimensional Ferm i surfaces at a high temperature have been claried for a strongly correlated Ce compound, ferror agnet CeRu₂Ge₂ in the param agnetic phase, by virtue of a soft x-ray h -dependent (700-860 eV) ARPES. A lthough the observed Ferm i surfaces as well as quasiparticle dispersions are partly explained by a band-structure calculation based on a localized 4f m odel, qualitative discrepancy in experiments, between our APRES in the param agnetic phase and de H aas-van A lphen measurement in the ferror agnetic phase, is revealed. This suggests a fundamental change in the 4f contribution to the Ferm i surfaces across the magnetic phase transition widely seen for Ce compounds.

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M any m acroscopic properties of solids such as resistivity, speci c heat and susceptibility depend strongly on momentum distribution of electrons on the chemical potential, namely, shapes and characters of the Fermi surfaces. Therefore, detection of the Ferm i surfaces is in portant to clarify the electronic properties of solids. The quantum oscillation measurement using de Haas-van Alphen (dHvA) e ect is known as a powerful technique to observe the cross-sections of the Ferm i surfaces [1]. The dHvA measurement has so farbeen applied also form any strongly correlated rare-earth m aterials [2, 3, 4]. Since the successful consistency between the experimentally observed Ferm i surfaces and the band-structure calculation assuming it inerant 4f electrons for CeSn₃ [5, 6], the dH vA m esurem ent has been recognized as a convincing tool to qualitatively judge whether the 4f electrons are "itinerant" or "localized" for the ground state of strongly correlated Ce com pounds. However, the Ferm i surfaces at high tem perature above several tens K, at which the electronic structures are often deviated from the ground state due to m agnetic phase transitions and/or the K ondo effect, have not been experim entally clari ed for many Ce com pounds because a low tem perature is required for the dHvA measurement. The low-h angle-resolved photoem ission spectroscopy (ARPES) is also useful to reveal the characters of the two-dimensional and/or surface Fermi surfaces as seen in the results for high-T_C cuprates[7]. As for the rare-earth com pounds, ARPES m easurem ents for XRu_2Si_2 (X = La, Ce, Th, U) have been performed by using h in a 14-230 eV range β]. Recently high-energy (h > 500 eV) photoem ission is found to be very e ective in probing bulk states [9, 10, 11, 12]. In this letter, we demonstrate the power of soft x-ray h -dependent ARPES for clari ng the bulk three-dimensional Ferm i surface topology of a strongly correlated rare-earth com pound, whose 4f electronic states are mutually di erent between the bulk and surface [10].

We have performed the ARPES measurements for $C \in Ru_2 G \in W$ high has one 4f electron per unit cell then we have compared with the band calculation for 4f electron localized m odel LaR u_2 G e_2 . C eR u_2 G e_2 is a requisite m aterial to understand the electronic states of C e heavy ferm ion system s because the rather localized 4f electrons becom e itinerant under high pressures [13]. $C \in Ru_2G e_2$ is a ferrom agnet with $T_c = 8 \text{ K} [14, 15]$ and the 4f electrons of $C \in Ru_2 G \in RKKY$ interaction is dom inant com pared with the K ondo e ect at low tem peratures with the electronic speci c heat coe cient of about 20 m J/m olK² [14] and the K ondo tem perature $T_K < 1 \text{ K}$ [16, 17]. CeRu₂Ge₂ crystallizes in a tetragonalThCr₂Si₂-type structure with a = 4.268 A and c=10.07 A at 18 K [14] and its B rillouin zone is shown in Fig. 1(a). On the other hand, isostructural CeRu₂Si₂ has it inerant 4f electrons with its low-tem perature electronic speci cheat coe cient of about 350 m J/m olK² [18] and 20 K [17]. These properties are consistent with the T_{K} bulk sensitive 3d - 4f resonant photoem ission results[10]. The larger lattice constant of $C \in Ru_2 G \in_2$ than that of CeRu₂Si₂ makes such di erent 4f electron properties.

CeRu₂Ge₂ single crystalwas grown by the Czochralski pulling m ethod. The high energy ARPES m easurem ents have been performed from h = 700 to 860 eV with an energy step of 5 eV at BL25SU in SPring-8[19]. The light incidence angle was 45 degrees with respect to the sample surface norm al. The base pressure was about 3 10 ⁸ Pa.W e have perform ed the m easurem ents at 20 K, where the sam ple was in the param agnetic phase. The clean surface was obtained by cleaving in situ providing a (001) plane. A GAMMADATA-SCENTA SES200 analyzer was used covering more than a whole Brillouin zone along the direction of the slit. The energy resolution was set to 200 m eV for Ferm i surface m apping. The cleanliness was con med by the absence of the 0 1s and C 1s photoem ission signals. First, we have perform ed $k_z = k_{xy}$

m apping at several h and angles. A fier determ ining the h corresponding to the high sym m etry points along the [001] direction, we have perform ed detailed angle-dependent ARPES for k_x k_y m apping. Then we have perform ed h dependent ARPES for k_z k_{xy} m apping through the high sym m etry points in the k_{xy} B rillouin zone.

In order to experimentally determ ine the exact value of kj we have taken the incident photon momentum into account. If x-ray was incident onto a sample at 45 degrees with respect to the surface normal, for example, this incident photon has the momentum parallel (q_k) and perpendicular (q_2) to the surface, which are $2 = \frac{p}{2}$ $(A^{-1})=2$ h (eV)=12398= $\frac{1}{2}$. In the case of h = 700 eV, the photon momentum values of both $jq_k j$ and $jq_2 j$ are about 0.25 A ⁻¹. Because the value $jk_z j$ of the 1st B rillouin zone of C eRu₂G e₂ (2 = c 0.62 A ⁻¹) is comparable to the value of the photon momentum, both q_k and q_2 cannot be negligible.

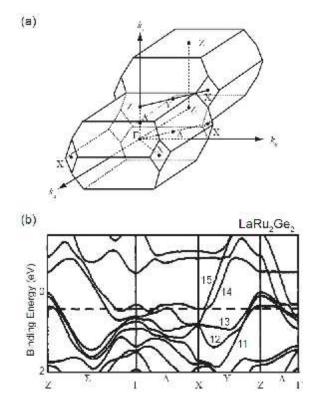


FIG.1: (a)The Brillouin zone of the body-centered tetragonal crystal $C \in Ru_2G \in Q$ with j Z = 2 = c. (b) The band calculation with APW method for $LaRu_2G \in Q$ [20]. The Ferm i surfaces are formed by 5 bands from 11 to 15.

The observed ARPES data have been compared with the band calculation of param agnetic $LaRu_2Ge_2$ perform ed by H.Yam agam iand A.Hasegawa [20] with using a sym m etrized relativistic augm ented-plane wave (APW) m ethod [21]. A coording to their calculation, ve bands (11 - 15) cut the Ferm i level (E_F) (Fig. 1(b)) form ing ve Ferm i surfaces which are composed of the La 4d and Ru 4d states. Five Ferm i surfaces are likewise derived for the itinerant 4f electron system $C eRu_2Si_2$ [2]. Between the localized LaRu_2Ge₂ and itinerant $C eRu_2Si_2$, the shapes of Ferm i surfaces derived from the bands 11 to 14 are not much di erent but the shape of the band 15 is mutually di erent. Am ong the calculated bands of LaRu_2Ge₂, the lower four bands from 11 to 14 form the hole-like Ferm i surfaces which are centered at the Z point in the B rillouin zone, and the highest band 15 form s the electron-like Ferm i sheet.

Figure 2(a) shows the energy distribution curves (EDCs) along the in-plane X - Z - X direction for $C \in R u_2 G \in C$. The positions of the wave number where each band cuts E_F is also estimated by the momentum distribution curves (M D C s). Five bands corresponding to the bands 11 to 15 predicted by the band calculation for $LaRu_2Ge_2$ are clearly seen. There is a clear peak near E_F at the Z point in Fig. 2 (a). The presence of this peak is in a strong contrast to the result of the band-structure calculation for LaR u₂G e₂, which predicts no quasiparticle peak near E_F at the Z point in Fig. 1(b). It is thus revealed that the band 11 is located on the occupied side and does not form the Ferm isurface. A though the band 15 does not cut E_F at the X point in the calculation for $LaRu_2Ge_2$, our experimental results show that the band 15 exists on the occupied side at the X point. Figure 2 (b) show sEDCs along the in-plane Z - - Z direction. The comparison between Fig. 1 (b) and Fig. 2 has shown the similarity of the observed bands 15 and 14 in C eR u_2 G e_2 with the result of the band calculation of $LaRu_2Ge_2$.

Figure 3 displays Ferm isurfaces' topology at $k_z = 2 = c$ by integrating the intensity around E_F of EDCs. The X – Z – X line corresponds to Fig. 2(a). The intensities around the Z point are due to the bands 11–13. We have clearly observed the sm all Ferm isurface contours around the Z point derived from both bands 12 and 13 and the large Ferm i surface contour derived from the band 14 as judged from Fig. 2(a). Furtherm ore, we recognize a sm all Ferm i surface contour centered at the X point. The possible origin of this sm all Ferm i surface is the band 15, whereas its E_F crossing is not predicted by the calculation for LaR u_2Ge_2 .

Figure 4 dem onstrates Ferm isurfaces' topology at k_z 0. The Z - -Z line corresponds to Fig.2(b). The very large Ferm i surface derived from the band 14 is clearly seen around the Z points. Furtherm ore a part of the Ferm i surface derived from the band 15, whose shape looks like a doughnut centered at the point according to the calculation for LaR u_2Ge_2 , can be traced.

M eanwhile, Fig. 5 shows the Ferm i surface slice at $k_z \ k_{xy}$ plane m easured with an energy step of 5 eV. In this gure are recognized the Ferm i surfaces 12 and 13 centered at the Z point, which are prolongated along the k_z direction. The very large Ferm i surface 14 com pressed vertically can be also experimentally traced. A long the horizontal X - -X direction, the band 15 cuts E_F near the and X points. The Ferm i surface of the band 15 is only partly observed near the point because of

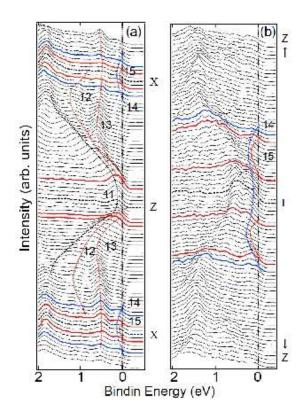


FIG.2: (color online) ARPES spectra near E_F of $CeRu_2Ge_2$ with an energy resolution of 200 meV. The dashed lines represent the bands corresponding to the APW calculation for LaRu_2Ge_2. (a) EDCs along the X - Z - X cut (h = 755 eV) shown in the third zone from the left in Fig. 1 (b). (b) EDCs along the Z - -Z cut (h = 820 eV) shown in the leftm ost zone of Fig. 1 (b).

the noticeable background. The nonnegligible intensities around the point and the Z point suggest the proximity of the band 14 and the band 11, respectively, which are not crossing E_F near these points but staying in the vicinity of E_F as we can see in Fig. 2. We have also observed the Ferm i surface continuing along the ordinate X -X axis derived from the band 15. In our Ferm i surface m apping, this Ferm i surface along the X -X axis in Fig. 5 is also detected near the X point in Fig. 3 corresponding to the upper X - Y - Z plane (Fig. 1(a)) and also near the X point in Fig. 4 corresponding to the middle - X plane (Fig. 1(a)).

The band calculation for LaR u_2Ge_2 predicts that there are three hole pockets derived from the band 11–13 and a large hole Ferm i surface derived from the band 14 centered at the Z point. In addition it predicts that the band 15 form s both a doughnut-like electron pocket centered at the point and a discontinuous Ferm i surface along the ordinate X - X direction. On the other hand, the dH vA m easurements for C eR u_2Ge_2 in the ferrom agnetic phase have con rm ed the existence of all Ferm i surface sheets spin-split[23, 24] corresponding to the bands 11– 15 predicted for LaR u_2Ge_2 . The agreement between the experimental Ferm i surfaces by dH vA and ARPES mea-

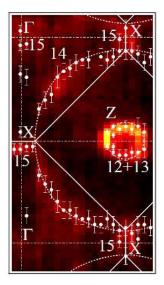


FIG. 3: (color online) Ferm i surface slice of CeR $u_2\,G\,e_2$ at $k_z \ 2 = c \ (h = 755 \ eV)$. Photoem ission intensity map was obtained by integrating the PES intensity from +0.1 eV to -0.1 eV. The solid lines represent the corresponding B rillouin zone and the dashed lines represent high symmetry lines. W hite dots (with error bars) represent the estimated k_F from EDCs and MDCs.

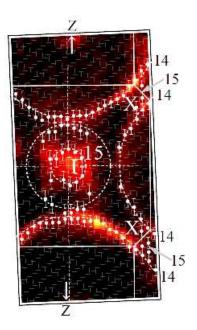


FIG.4: (color online) Ferm isurface slice of CeRu₂Ge₂ at k_z 0 (h = 820 eV). Photoem ission intensity map was obtained by integrating the PES intensity from +0.1 eV to -0.1 eV.

surem ents and the calculated results is quite good for the bands 12, 13 and 14.

From our ARPES results, however, the Ferm i surface of C eR u_2 G e_2 derived from the band 11 is found not to exist as revealed in F ig. 2 (a). It is also found that the band 15 has a continuous Ferm i surface along the k_z direction in the param agnetic phase. These results are in a strong

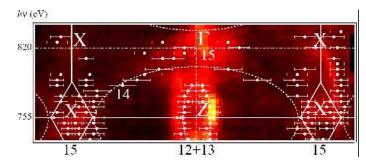


FIG. 5: (color online) Ferm i surface slice in k_z (ordinate) – k_{xy} (abscissa) plane. Photon energies were changed from 735 eV to 840 eV.h = 820 eV and 755 eV correspond to the point and the Z points, respectively, along the -Z direction corresponding to the right most zone in Fig.1 (b). The upper horizontalX - -X axis corresponds to the second zone from the left in Fig. 1 (b). Photoem ission intensity m ap was obtained by integrating the PES intensity from + 0.1 eV to -0.1 eV.

contrast to the dH vA results in the ferrom agnetic phase. A lthough the Ferm i surface of $C eR u_2 G e_2$ in the ferrom agnetic phase is similar to that of LaR $u_2 G e_2$, the dierence of our ARPES results from them are consistently understood if E_F of $C eR u_2 G e_2$ in the param agnetic phase is energetically higher than that of the calculation for LaR $u_2 G e_2$. E_F shift of $C eR u_2 G e_2$ in the param agnetic phase from LaR $u_2 G e_2$ or $C eR u_2 G e_2$ in the ferrom agnetic phase is thought to be due to the increased number of the electrons contributing to the near E_F bands in $C eR u_2 G e_2$, where the weak but nonnegligible hybridization of the Ce 4f electron should be additionally taken into account in the param agnetic phase. The dierence of the electric resistivity between $C eR u_2 G e_2$ and LaR $u_2 G e_2$

is suddenly diminished below $T_{\rm C}\,$ of C eR u_2 G e_2 [14], indicating the reduction of electron scattering by the ferrom agnetic ordering. This suggests that the contribution of the 4f electrons to the Ferm i surfaces due to the hybridization is reduced in the ferrom agnetic phase. Then the number of the electrons contributing to the Ferm i surfaces decreases below $T_{\rm C}$. A coordingly, the band 11 crosses $E_{\rm F}\,$ near the Z point and the band 15 m ight form discontinuous Ferm i surfaces along the X -X ($k_{\rm Z}$) direction as predicted by the band-structure calculation.

We have performed three-dimensional bulk-sensitive ARPES measurements for paramagnetic $C \in Ru_2 G \in Q$ by using soft x-rays. Although the Fermi surfaces obtained for the bands 12, 13 and 14 are in good agreement with the result of the band calculation for param agnetic $LaRu_2Ge_2$, the predicted band 11 is found to be not contributing to the Ferm i surface in param agnetic $C \in Ru_2 G \in_2$. The band 15 is con med to have the doughnut-like shape around the point whereas a rodlike continuous Ferm i surface along the X - X axis is observed in a strong contrast to the band calculation. The slight hybridization in the param agnetic phase and the magnetic ordering below T_C are thought to be essential to understand the behaviors of three-dim ensional electronic structures of $C \in \mathbb{R}$ u₂ $G \in_2$.

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- N.W. Ashcroft, and N.D. Mermin, 1976, Solid State Physics (Saunders College, Philadelphia).
- [2] H. Yam agam i and A. Hasegawa, J. Phys. Soc. Jpn. 60, 1011 (1991).
- [3] P. H. P. Reinders, M. Springford, P. T. Coleridge, R. Boulet, and D. Ravot, Phys. Rev. Lett. 57, 1631 (1986).
- [4] G.Zwicknagl, Adv.Phys.41, 203 (1992).
- [5] W.R.Johanson, G.W.Crabtree, A.S.Edelstein and O.
 D.M cM asters, Phys. Rev. Lett. 46, 504 (1981).
- [6] A.Hasegawa et al., J.Phys.Soc.Jpn.59, 2457 (1990).
- [7] A. Dam ascelli, Z. Hussain, and Z.-X. Shen, Rev. Mod. Phys. 75, 473 (2003).
- [8] JD. Denlinger et al., J. Electron Spectrosc. Relat. Phenom. 117, 347 (2001).
- [9] A. Sekiyam a et al., Nature (London) 403, 396 (2000).
- [10] A.Sekiyam a et al, J.Phys.Soc.Jpn.69, 2771 (2000).
- [11] A.Sekiyam a et al, Phys.Rev.B 70,060506(R) (2004).
- [12] S.Suga et al, Phys. Rev. B 70, 155106 (2004).
- [13] H.W ilhelm and D. Jaccard, Phys. Rev. B 69, 214408

(2004).

- [14] M J. Besnus et al., Physica B 171, 350 (1991).
- [15] A. Bohm et al., J. Magn. Magn. Mater. 76-77, 150 (1988).
- [16] A.Loidlet al, Phys. Rev. B 46, 9341 (1992).
- [17] A.Loidl, G.Knopp, H.Spille, F.Steglich, A.P.Murani, Physica B 156, 794 (1989).
- [18] G.G.Lonzarich, J.M agn.M agn.M ater. 76-77, 1 (1988).
- [19] Y. Saitoh et al., J. Synchrotron Rad. 5, 542 (1998).
- [20] H. Yam agam i and A. Hasegawa, J. Phys. Soc. Jpn. 63, 2290 (1994).
- [21] H. Yam agam i and A. Hasegawa, J. Phys. Soc. Jpn. 59, 2426 (1990).
- [22] H. Yam agam i and A. Hasegawa, J. Phys. Soc. Jpn. 62, 592 (1993).
- [23] C A.K ing and G G.Lonzarich, Physica B 171, 161-165 (1991).
- [24] H. Ikezawa et al., Physica B 237, 210 (1997).